

JACOBSON HOLMAN PLLC
400 SEVENTH STREET, N.W.
WASHINGTON, D.C. 20004-2201

ANYA, I
2891

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.: P69577US0 GROUP ART UNIT: Not Yet Assigned
 SERIAL NO.: New Application 10/800,680 FILING DATE: March 16, 2004
 APPLICANT(S): Hyun Woo SONG et al. TODAY'S DATE: March 16, 2004

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	INT'L CLASS	SUB- CLASS	FILING DATE (If Appropriate)
IA	AA 5,068,868	11/26/91	Deppe, et al.	H01S	3/19	5/21/90
IA	AB 6,121,068	09/19/00	Ramdani, et al.	H01L	21/00	3/26/98
IA	AC 5,711,811	1/27/98	Suntola et al.	C32C	16/00	11/28/95

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION (YES) (NO)
IA	AD 11-307863	11/05/99	JAPAN	H01S	3/18	X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

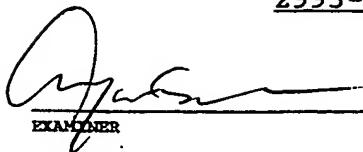
IA	AE	<u>Chao-Kun Lin, et al; "Electrically pumped 1.3 VCSELs with InP/air-gap DBRs"; CLEO '02 Lasers and Electro-optics, 2002.; pp. 755-757.</u>				
IA	AF	<u>Chao-Kun Lin, et al; "High temperature continuous-wave operation of 1.3-1.55 um VCSELs with InP/air-gap DBRs"; IEEE 18th International Semiconductor Laser Conference 2002; pp. 145-146.</u>				
IA	AG	<u>I.Gagnes, et al; "MOCVD InP/AlGaInAs distributed Bragg reflector for 1.55um VCSELs"; Electronics Letters 12th April 2001, Vol. 37, No. 8; pp. 500-501.</u>				
IA	AH	<u>J.-H.Shin, et al; "CW Operation and Threshold Characteristics of All-Monolithic InAlGaAs 1.55-um VCSELs Grown by MOCVD"; IEEE Photonics Technology Letters, Vol. 14, No. 8; August 2002; pp. 1031-1033.</u>				
IA	AI	<u>K. Streubel, et al; "1.26um vertical cavity laser with two InP/air-gap reflectors"; Electronics Letters 18th July 1996, Vol. 32, No. 15; pp. 1369-1370.</u>				

ITA

AJ : Hyun-Eoi SHIN, et al; "High-finesse Al_xO_y/AlGaAs nonabsorbing optical cavity"; Applied Physics Letters; Vol. 72. No. 18; May 4, 1998; pp. 2205-2207.

IA

AH : Sun Jin Yun, et al; "Dependence of atomic layer-deposited Al₂O₃ films characteristics on growth temperature and Al precursors of Al(CH₃)₃ and AlCl₃"; J.Vac.Sci. Technol. A 15(6), Nov/Dec 1997; pp. 2993-2997.



EXAMINER

DATE CONSIDERED

3/20/05

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).